

ABSTRACT OF THE DISCLOSURE

The present invention is; (a) a process for stabilizing a cyclotetrasiloxane,
5 such as 1,3,5,7-tetramethylcyclotetrasiloxane, against polymerization used in a
chemical vapor deposition process for silicon oxides in electronic material
fabrication comprising providing an effective amount of a free radical scavenger
polymerization inhibitor to such cyclotetrasiloxane; and (b) a composition of a
cyclotetrasiloxane, such as 1,3,5,7-tetramethylcyclotetrasiloxane, stabilized
10 against polymerization used in a chemical vapor deposition process as a
precursor for silicon oxides in electronic material fabrication, comprising; such
cyclotetrasiloxane and a free radical scavenger polymerization inhibitor.

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